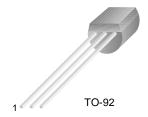


### **BF199**

### **NPN RF Transistor**



1. Collector 2. Emitter 3. Base

# **Absolute Maximum Ratings\*** $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	25	V
V <sub>CBO</sub>	Collector-Base Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	4.0	V
I <sub>C</sub>	Collector Current - Continuous	50	mA
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- These ratings are based on a maximum junction temperature of 150 degrees C.
   These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

# Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Charact	eristics	•	•	•	•
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage *	$I_C = 1.0 \text{mA}, I_B = 0$	25		V
V <sub>(BR)CBO</sub>	Collector-Base BreakdownVoltage	$I_C = 100\mu A, I_E = 0$	40		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	4.0		V
I <sub>CES</sub>	Collector Cut-off Current	$V_{CE} = 30V, I_{E} = 0$		50	nA
On Characte	eristics	•	•	•	•
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 7.0mA, V <sub>CE</sub> = 10V	38		
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = 10 \text{mA}, I_B = 5.0 \text{mA}$		0.2	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	$I_C = 10 \text{mA}, I_B = 5.0 \text{mA}$		0.92	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	I <sub>C</sub> = 7.0mA, V <sub>CE</sub> = 10V		0.925	V
Small Signa	I Characteristics		•		
f <sub>T</sub>	Current gain Bandwidth Product	$I_C = 7.0 \text{mA}, V_{CE} = 10 \text{V},$ f = 100 MHz		1100	MHz
C <sub>re</sub>	Common-Emitter Ruerse Transfer Capacitance	$V_{CB} = 10V, I_{E} = 0, f = 1.0MHz$		0.4	pF

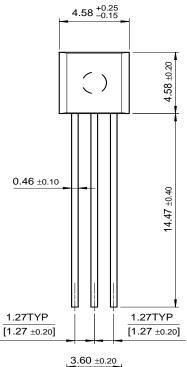
<sup>\*</sup> Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2.0%

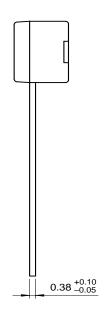
# Thermal Characteristics $T_A=25$ °C unless otherwise noted

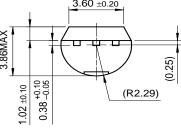
Symbol	Parameter	Max.	Units	
P <sub>D</sub>	Total Device Dissipation	350	mW	
	Derate above 25°C	2.8	mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W	

# **Package Dimensions**

TO-92







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